

# ESD7C, SZESD7C SERIES

## ESD Protection Diode

### Micro-Packaged Diodes for ESD Protection

The ESD7CxxD Series is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, portable devices, digital cameras, power supplies and many other portable applications.

#### Specification Features:

- Low Capacitance 6.2 pF to 13 pF
- Low Clamping Voltage
- Small Body Outline Dimensions:  
0.047" x 0.047" (1.20 mm x 1.20 mm)
- Low Body Height: 0.020" (0.5 mm)
- Stand-off Voltage: 3.3 V, 5 V
- Low Leakage
- Response Time < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

#### Mechanical Characteristics:

**CASE:** Void-free, transfer-molded, thermosetting plastic

Epoxy Meets UL 94 V-0

**LEAD FINISH:** 100% Matte Sn (Tin)

**MOUNTING POSITION:** Any

**QUALIFIED MAX REFLOW TEMPERATURE:** 260°C

Device Meets MSL 1 Requirements

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Contact Air		±8.0 ±15	kV
Total Power Dissipation on FR-5 Board (Note 1) @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	240 1.9	mW mW/°C
Thermal Resistance Junction-to-Ambient	R <sub>θJA</sub>	525	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Lead Solder Temperature - Maximum (10 Second Duration)	T <sub>L</sub>	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

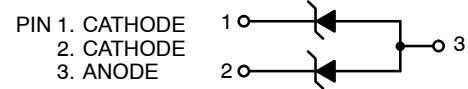
1. FR-5 = 1.0 x 0.75 x 0.62 in.

See Application Note AND8308/D for further description of survivability specs.



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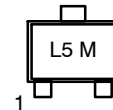
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#### MARKING DIAGRAM



SOT-723  
CASE 631AA



L5 = Specific Device Code  
M = Date Code

\*Date Code orientation and/or position may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
ESD7CxxDT5G	SOT-723 (Pb-Free)	8000 / Tape & Reel
SZESD7CxxDT5G	SOT-723 (Pb-Free)	8000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the table on page 2 of this data sheet.

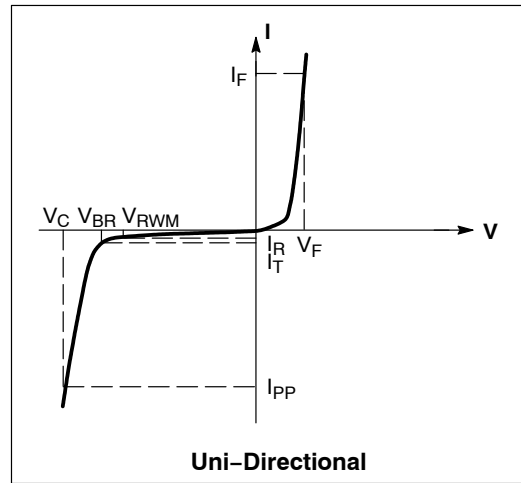
# ESD7C, SZESD7C SERIES

## ELECTRICAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Working Peak Reverse Voltage
$I_R$	Maximum Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$
$P_{pk}$	Peak Power Dissipation
C	Max. Capacitance @ $V_R = 0$ and $f = 1$ MHz

\*See Application Note AND8308/D for detailed explanations of datasheet parameters.



## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 1.1$ V Max. @ $I_F = 10$ mA)

Device (Note 2)	Device Marking	$V_{RWM}$ (V)	$I_R$ ( $\mu\text{A}$ ) @ $V_{RWM}$	$V_{BR}$ (V) @ $I_T$ (Note 3)	$I_T$	C (pF) (Note 4)	C (pF) (Note 4)	$V_C$ Per IEC61000-4-2 (Note 5)
		Max	Max	Min	mA	Typ	Max	
ESD7C3.3DT5G	L5	3.3	1.0	5.0	1.0	12	13	Figures 1 and 2 See Below (Note 6)
ESD7C5.0DT5G	L4	5.0	0.5	11	1.0	6.0	6.2	

2. Include SZ-prefix devices where applicable.
3.  $V_{BR}$  is measured with a pulse test current  $I_T$  at an ambient temperature of  $25^\circ\text{C}$ .
4. Capacitance of one diode at  $f = 1$  MHz,  $V_R = 0$  V,  $T_A = 25^\circ\text{C}$ .
5. For test procedure see Figures 3 and 4 and Application Note AND8307/D.
6. ESD7C5.0DT5G shown below. Other voltages available upon request.

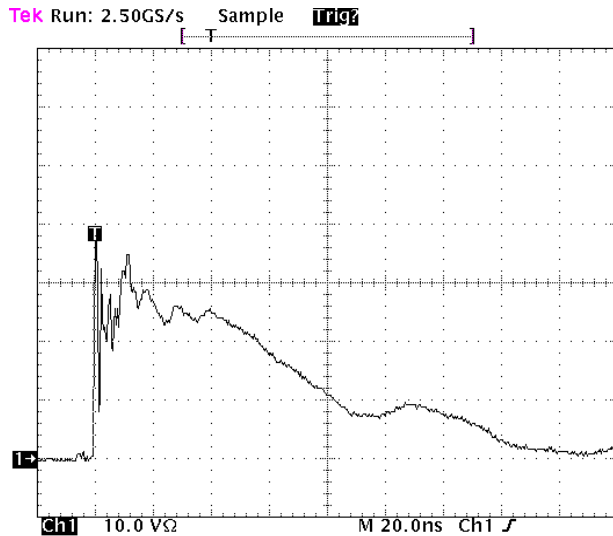


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2

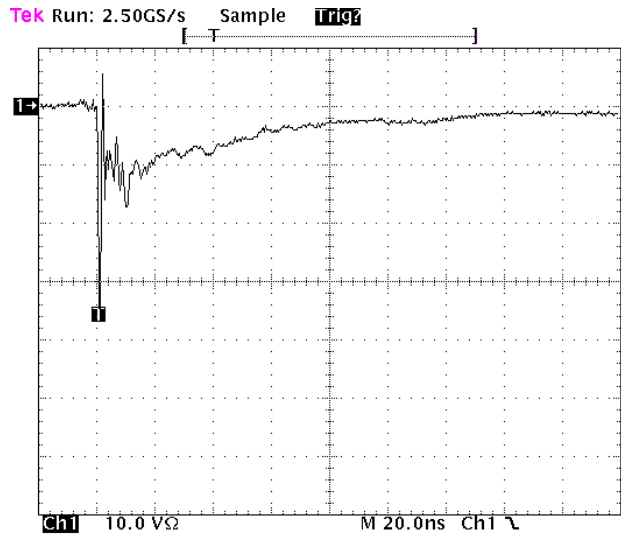


Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2

## ESD7C, SZESD7C SERIES

IEC 61000-4-2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8



Figure 3. IEC61000-4-2 Spec

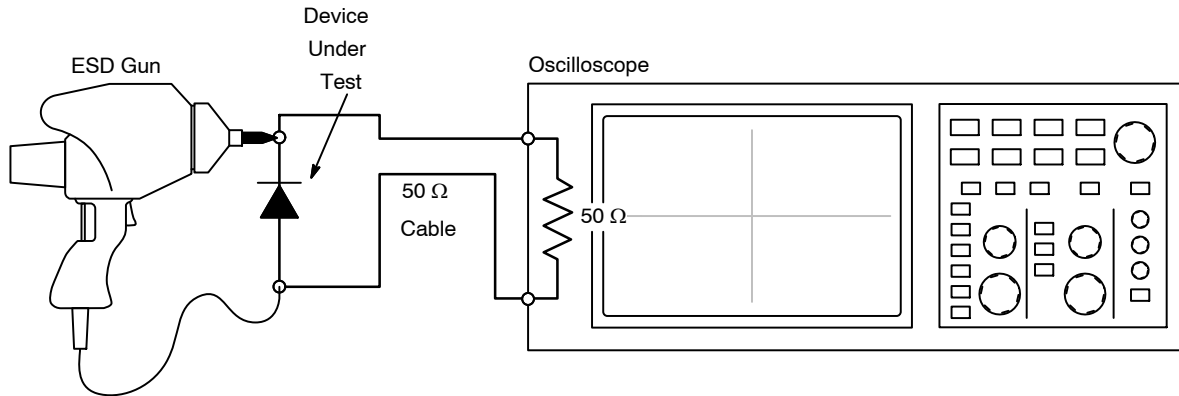


Figure 4. Diagram of ESD Test Setup

The following is taken from Application Note AND8308/D – Interpretation of Datasheet Parameters for ESD Devices.

### ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger

systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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SCALE 4:1

**SOT-723**  
CASE 631AA-01  
ISSUE D

DATE 10 AUG 2009

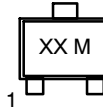


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

**GENERIC MARKING DIAGRAM\***



XX = Specific Device Code  
M = Date Code

- |   |  |  |  |  |
|---|--|--|--|--|
| STYLE 1:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 2:<br>PIN 1. ANODE<br>2. N/C<br>3. CATHODE | STYLE 3:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE | STYLE 4:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE | STYLE 5:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN |
|---|--|--|--|--|

**RECOMMENDED SOLDERING FOOTPRINT\***



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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